

SILICON NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF264** is Designed for Class C VHF Mobile Radio Power Amplifier Applications Operating at 12.5 Volts.

FEATURES:

- $P_{OUT} = 30\text{ W Min. @ } 175\text{ MHz}$
- Gold Metalization
- Economical **TO-220 CE** Package

MAXIMUM RATINGS

I_C	6.0 A
V_{CE}	16 V
P_{DISS}	80 W @ $T_C = 25^\circ\text{C}$
T_J	$-65^\circ\text{C to } +200^\circ\text{C}$
T_{STG}	$-65^\circ\text{C to } +150^\circ\text{C}$
θ_{JC}	1.6 $^\circ\text{C/W}$

PACKAGE STYLE TO-220

	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.6	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037

1 = BASE 2 = EMITTER 3 = COLLECTOR
MOUNTING TAB = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 20\text{ mA}$	16			V
BV_{CES}	$I_C = 20\text{ mA}$	36			V
BV_{EBO}	$I_E = 5.0\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 15\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	20	50		---
C_{OB}	$V_{CB} = 15\text{ V}$ $f = 1.0\text{ MHz}$			20	pF
P_G	$V_{CE} = 12.5\text{ V}$ $P_{OUT} = 30\text{ W}$ $f = 175\text{ MHz}$	5.2			dB
η_c		60			%